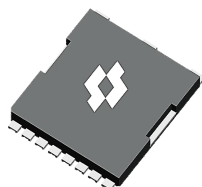
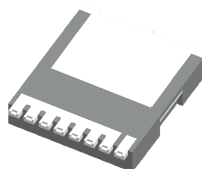


Product Summary

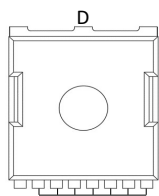
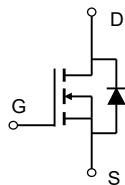
V_{DS}	$R_{DS(ON_TYP)}$	I_{D_MAX}
100 V	1.2 m Ω @ $V_{GS} = 10V$	375 A

TOLL


Top View



Bottom View


 PIN Configuration
(Top View)


Schematic Diagram

Features

- Low On-Resistance
- Excellent FoM (figure of merit)
- 100% ΔV_{DS} & UIS & Rg Tested


**HALOGEN
FREE**
Applications

- DC/DC in Telecoms and Industrial
- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit

Mechanical Data

- Green Molding Compound
- Moisture Sensitivity: Level 1 per J-STD-020
- UL Flammability Classification Rating 94V-0

Ordering Information

Orderable Part Number	Package Type	Device Marking	Form	Quantity (pcs)
SMT10T01EHTL2	TOLL	10T01EH2	13" Tape&Reel	2,000

Maximum Ratings (@ $T_C = 25^\circ\text{C}$, unless otherwise specified.)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	100	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($V_{GS} = 10V$) ⁽¹⁾	I_D	375	A
		237	A
Pulsed Drain Current ⁽²⁾	I_{DM}	1502	A
Single Pulse Avalanche Energy ⁽³⁾	E_{AS}	1904	mJ
Single Pulse Avalanche Current ($L = 0.3mH$)	I_{AS}	74	A
Power Dissipation	P_D	357	W
		143	W
Junction & Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

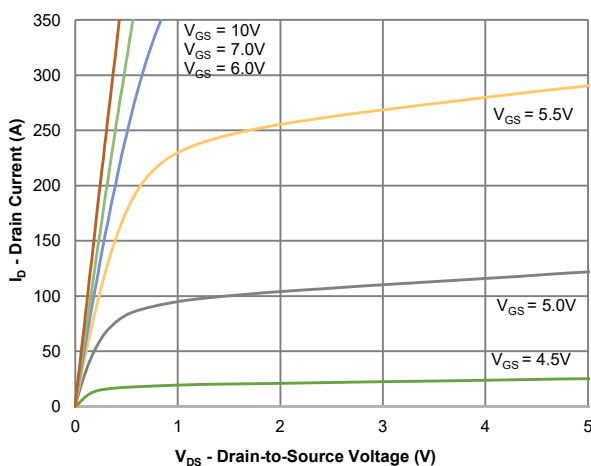
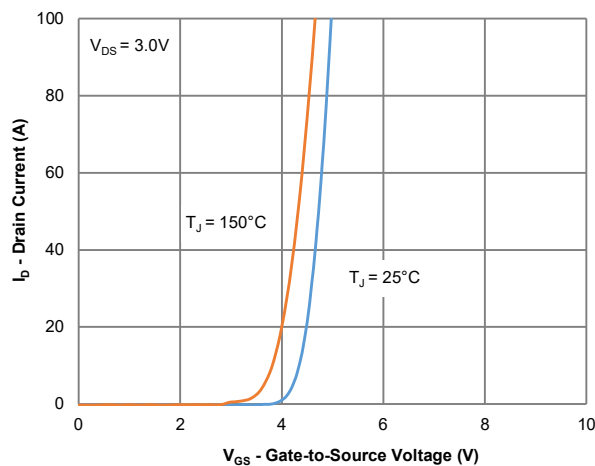
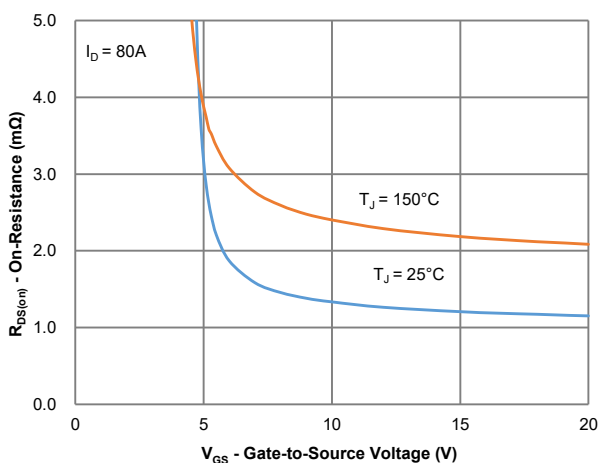
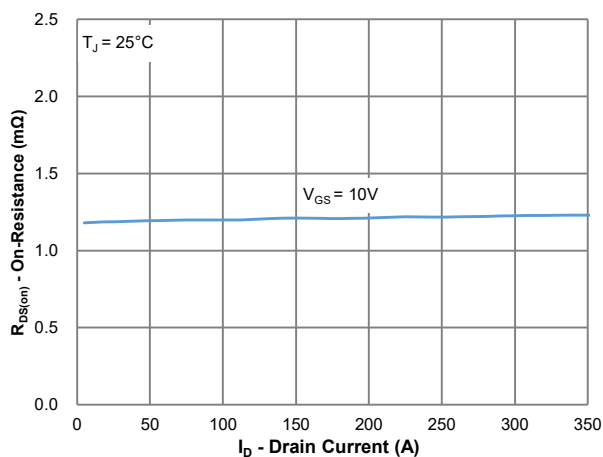
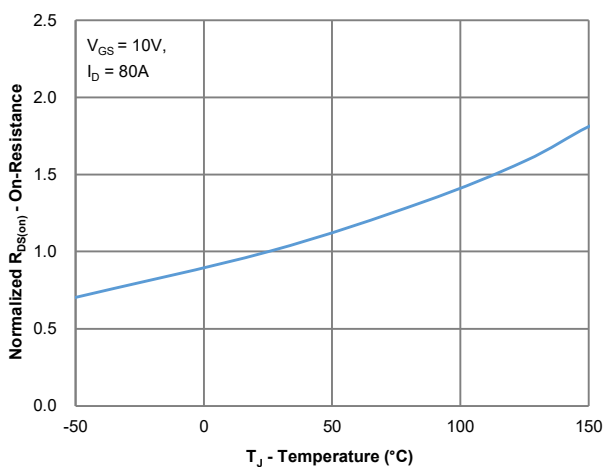
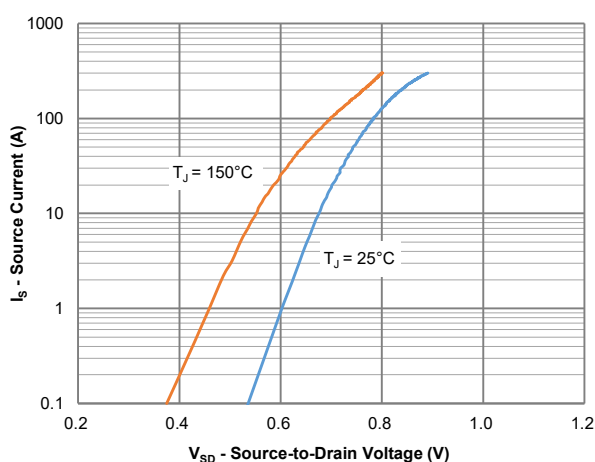
Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient ⁽⁴⁾	$R_{\theta JA}$	23	29	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case ⁽⁵⁾	$R_{\theta JC}$	0.27	0.35	$^\circ\text{C/W}$

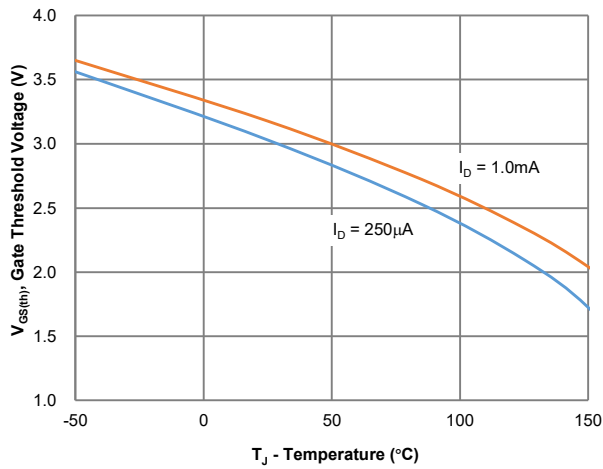
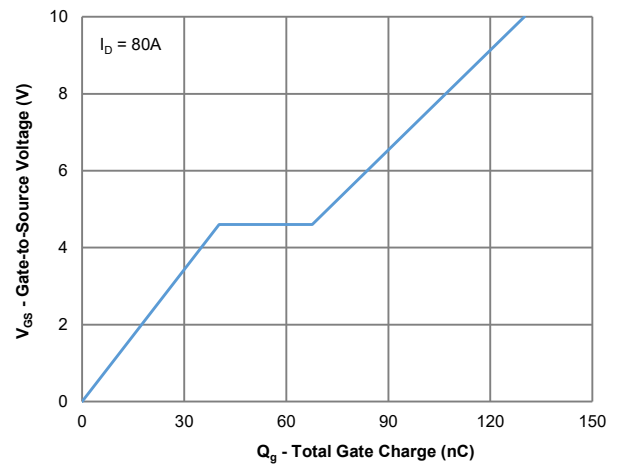
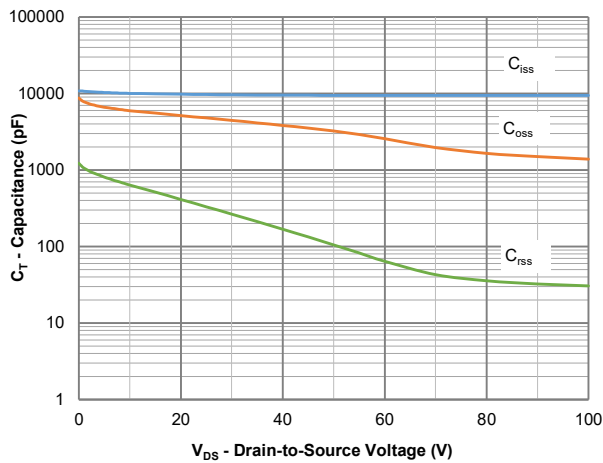
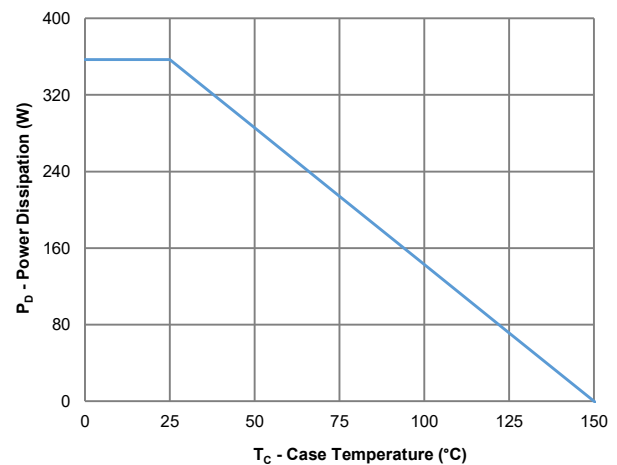
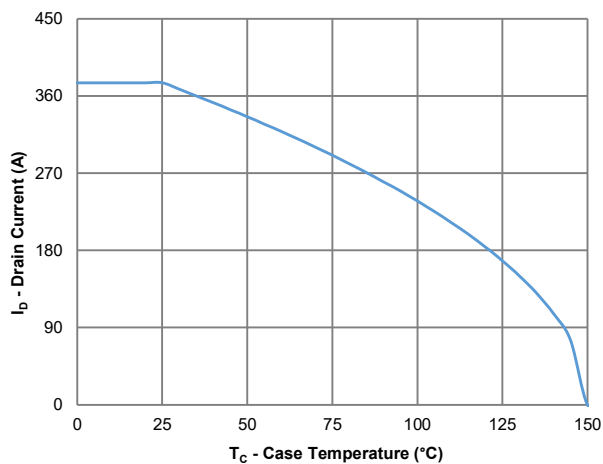
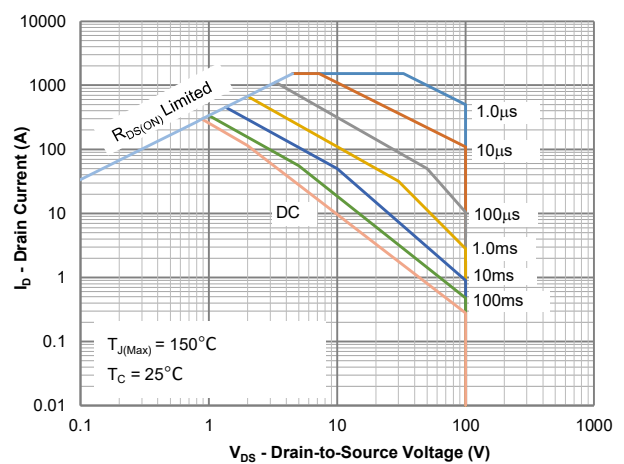
Electrical Characteristics (@ $T_J = 25^\circ\text{C}$, unless otherwise specified.)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Off Characteristics ⁽⁶⁾						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V	-	-	1.0	μA
		T _J = 125°C	-	-	100	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
On Characteristics ⁽⁶⁾						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	2.0	3.0	4.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 80A	-	1.2	1.4	mΩ
Forward Transconductance	g _{fs}	V _{DS} = 5.0V, I _D = 20A	-	75	-	S
Diodes Forward Voltage	V _{SD}	I _S = 2.0A, V _{GS} = 0V	-	0.7	1.2	V
Dynamic Characteristics ⁽⁷⁾						
Input Capacitance	C _{iss}	V _{DS} = 50V, V _{GS} = 0V, f = 1MHz	-	9471	-	pF
Output Capacitance	C _{oss}		-	3226	-	pF
Reverse Transfer Capacitance	C _{rss}		-	105	-	pF
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	-	1.3	-	Ω
Switching Characteristics ⁽⁷⁾						
Turn-On DelayTime	t _{d(on)}	V _{GS} = 10V, V _{DS} = 50V I _D = 80A, R _{GEN} = 3.0Ω	-	21	-	ns
Rise Time	t _r		-	31	-	ns
Turn-Off DelayTime	t _{d(off)}		-	57	-	ns
Fall Time	t _f		-	33	-	ns
Gate Charge Characteristics ⁽⁷⁾						
Total Gate Charge (V _{GS} = 10V)	Q _g	V _{DS} = 50V, I _D = 80A V _{GS} = 10V	-	130	-	nC
Total Gate Charge (V _{GS} = 7.0V)	Q _g		-	95	-	nC
Gate-Source Charge	Q _{gs}		-	40	-	nC
Gate-Drain Charge	Q _{gd}		-	27	-	nC
Gate Plateau Voltage	V _{plateau}		-	4.6	-	V
Drain-Source Diode Characteristics ⁽⁷⁾						
Body Diode Reverse Recovery Time	t _{rr}	I _F = 80A, dI/dt = 100A/μs, T _J = 25°C	-	82	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	162	-	nC
Diode Forward Current	I _S	T _C = 25°C	-	-	375	A

Notes:

1. This current is chip limited, which is calculated based on R_{thjc} .
2. This current is calculated on single pulse with 10us Single Pulse.
3. Defined by design, not subject to production test, E_{AS} condition: $T_J = 25^\circ\text{C}$, $V_{DS} = 50V$, $V_{GS} = 10V$, $L = 1.0\text{mH}$.
4. Device mounted on FR-4 substrate PC board with 2oz copper in 1inch square cooling area.
5. Thermal resistance from junction to the exposed pad.
6. Short duration pulse test used to minimize self-heating effect.
7. Defined by design, not subject to production.

Typical Electrical and Thermal Characteristics

Figure 1: Output Characteristics

Figure 2: Transfer Characteristics

Figure 3: On-Resistance vs. Gate-Source Voltage

Figure 4: On-Resistance vs. Drain Current and Gate Voltage

Figure 5: On-Resistance vs. Junction Temperature

Figure 6: Source-Drain Diode Forward Voltage

Typical Electrical and Thermal Characteristics

Figure 7: Gate Threshold Variation vs. Junction Temperature

Figure 8: Gate Charge Characteristics

Figure 9: Capacitance Characteristics

Figure 10: Power Derating

Figure 11: Current Derating

Figure 12: Safe Operating Area

Typical Electrical and Thermal Characteristics

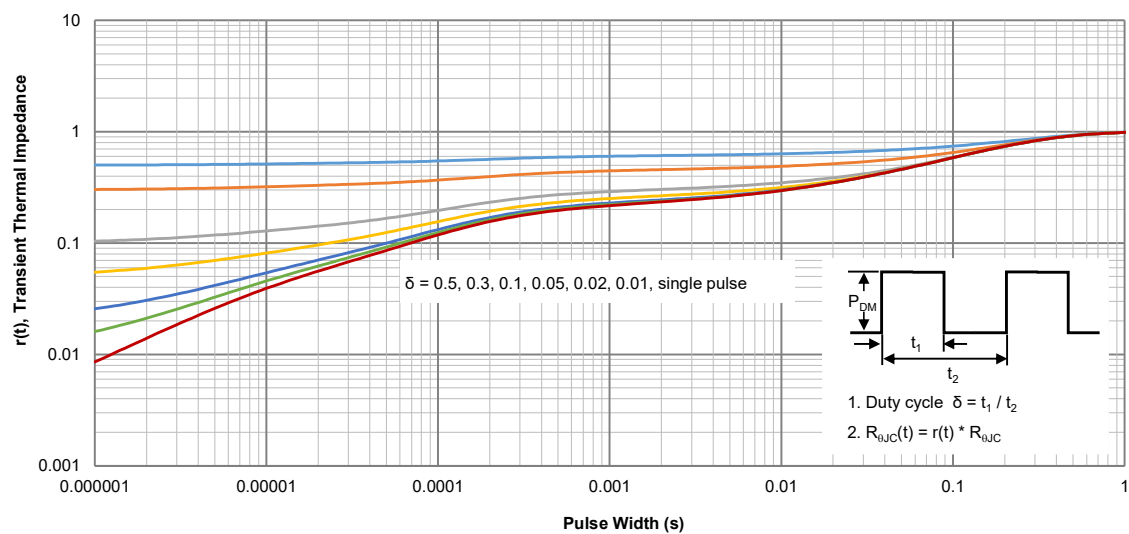
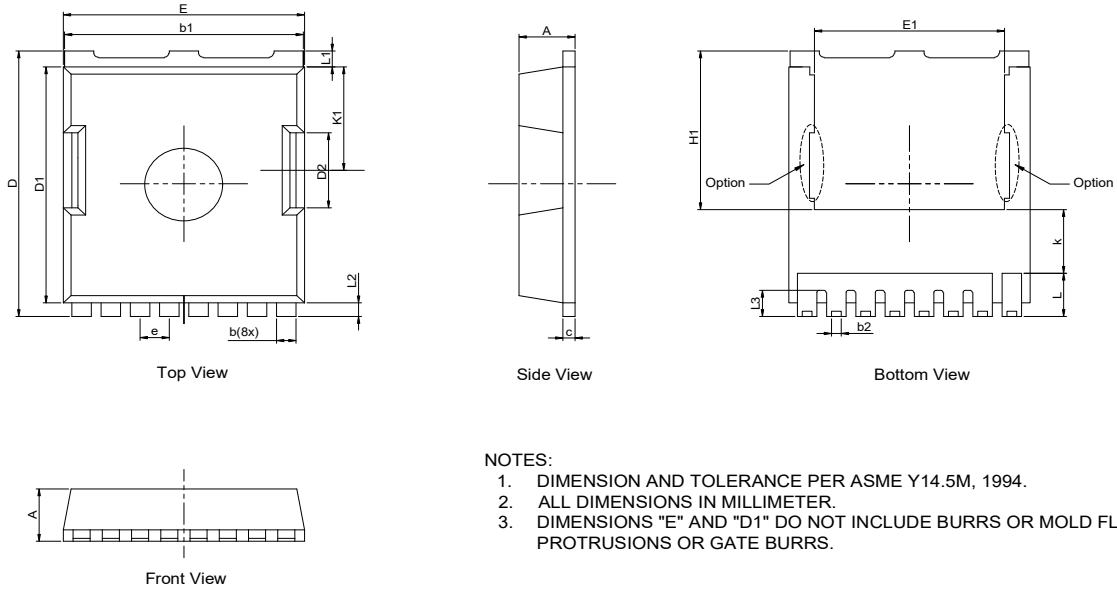


Figure 13: Normalized Maximum Transient Thermal Impedance

TOLL Package Outline
Package Outlines

NOTES:

1. DIMENSION AND TOLERANCE PER ASME Y14.5M, 1994.
2. ALL DIMENSIONS IN MILLIMETER.
3. DIMENSIONS "E" AND "D1" DO NOT INCLUDE BURRS OR MOLD FLASH. PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.200	2.300	2.400
b	0.650	0.800	0.900
b1	9.650	9.800	9.950
b2	0.400 REF		
c	0.400	0.500	0.600
D	11.480	11.680	11.950
D1	10.250	--	10.700
D2	2.850	--	3.400
E	9.700	9.900	10.100
E1	8.000	--	9.250
e	1.200 BSC		
H1	6.700	7.000	7.300
k	3.000 REF		
k1	4.550 REF		
L	1.350	--	2.100
L1	0.700 REF		
L2	0.600 REF		
L3	0.950	1.200	1.350

Recommended Soldering Footprint
